

Effect of Si(111) surface modification by Ga focused ion beam at 30 kV on GaAs nanowire growth

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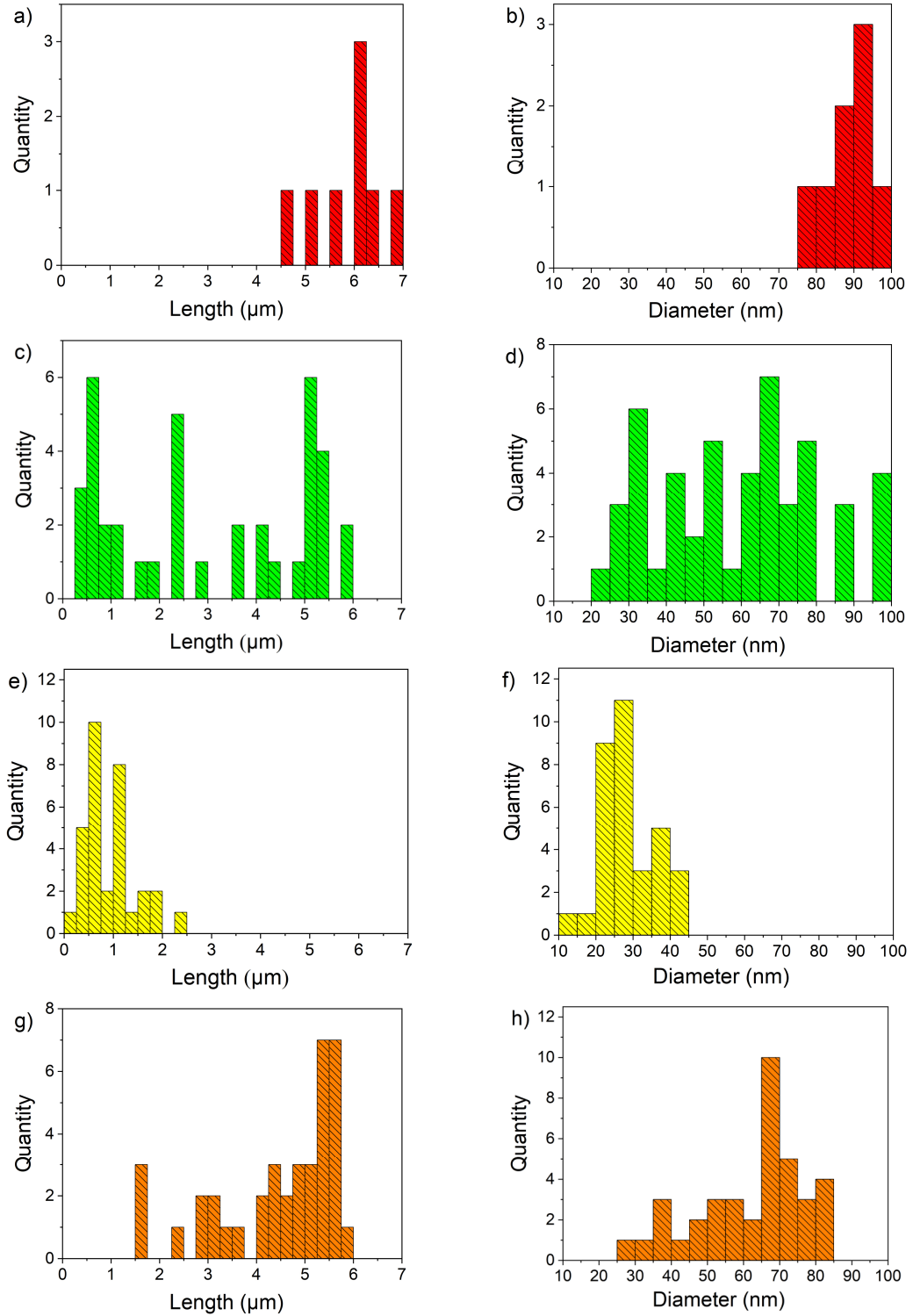


Figure S1. Histograms of NW length and diameters distribution for: (a, b) area I (0.052 pC/μm²); (c, d) area II (0.26 pC/μm²); (e, f) area III (10.4 pC/μm²); (g, h) unmodified area.